

## **INCHANGE SEMICONDUCTOR**

## **isc Silicon PNP Power Transistors**

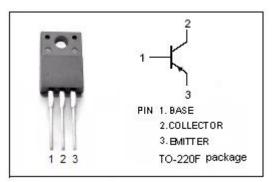
## **MJF45H11**

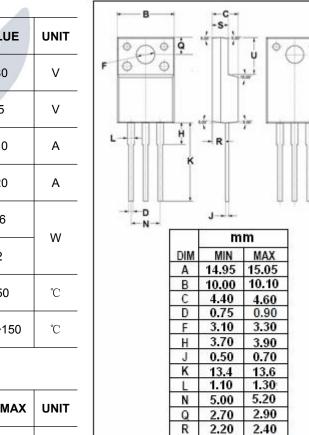
### DESCRIPTION

- Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= -1.0V(Max.)@ I<sub>C</sub>= -8A
- Fast Switching Speeds
- Complement to Type MJF44H11
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

• Designed for general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifier.





## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CEO</sub>	Collector-Emitter Voltage	-80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
Ic	Collector Current-Continuous	-10	А	
I <sub>CM</sub>	Collector Current-Peak	-20	A	
Pc	Collector Power Dissipation @Tc=25℃	36	W	
	Collector Power Dissipation @T <sub>a</sub> =25°C	2		
Tj	Junction Temperature 15		°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

#### **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	3.5	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	62.5	°C/W

S

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2.65

6.40

2.90

6.60

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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -8A; I <sub>B</sub> = -0.4 A			-1.0	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = -8A; I <sub>B</sub> = -0.8 A			-1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> =Rated V <sub>CEO</sub> ;			-1.0	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	μA
hfe-1	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> = -1V	60			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> = -1V	40			



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